



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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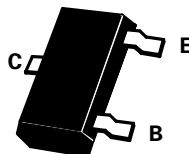
SOT23 NPN SILICON PLANAR MEDIUM POWER TRANSISTOR

BCX19

ISSUE 4 – MARCH 2001

PARTMARKING DETAILS – BCX19 - U1
BCX19R - U4

COMPLEMENTARY TYPES - BCX17



SOT23

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	V_{CES}	50	V
Collector-Emitter Voltage	V_{CEO}	45	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Current	I_{CM}	1000	mA
Continuous Collector Current	I_C	500	mA
Base Current	I_B	100	mA
Peak Base Current	I_{BM}	200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{TOT}	330	mW
Operating and Storage Temperature Range	$T_j:T_{stg}$	-55 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Cut-Off Current	I_{CBO}			100 200	nA μA	$V_{CB}=20V$ $V_{CB}=20V, T_j=150^{\circ}C$
Emitter-Base Cut-Off Current	I_{EBO}			10	μA	$V_{EB}=5V$
Base-Emitter Voltage	V_{BE}			1.2	V	$I_C=500mA, V_{CE}=1V^*$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			620	mV	$I_C=500mA, I_B=50mA^*$
Static Forward Current Transfer Ratio	h_{FE}	100 70 40		600		$I_C=100mA, V_{CE}=1V$ $I_C=300mA, V_{CE}=1V^*$ $I_C=500mA, V_{CE}=1V^*$
Transition Frequency	f_T		200		MHz	$I_C=10mA, V_{CE}=5V$ $f=35MHz$
Output Capacitance	C_{obo}		5.0		pF	$V_{CB}=10V, f=1MHz$

*Measured under pulsed conditions.